

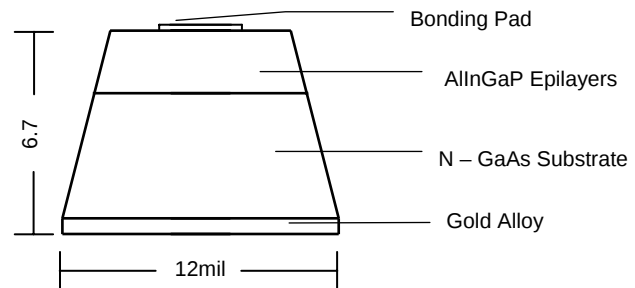
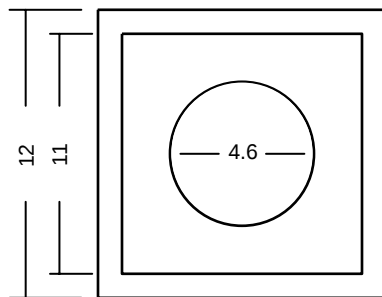
TCE12URU-S



❖ Features:

- AlInGaP/GaAs LED Chips
- High Driving Current Application
- High Luminous Intensity
- Low Power Consumption
- Indoor/Outdoor applications
- 100% Probing Test

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	12 mil x 12 mil	305 μm x 305 μm
		Thickness	6.7 mil	170 μm
		Emission area	11 mil	279 μm
		Bonding pad	4.6 mil	117 μm
Electrode	Top	P (anode)	Gold alloy	
	Backside	N (cathode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symb ol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 10\mu\text{A}$	1.30	-	-	V
		$I_F = 20\text{mA}$	-	2.00	2.40	
Wavelength	λ_P	$I_F = 20\text{mA}$		632		nm
	Hue	$I_F = 20\text{mA}$	619	624	629	
Spectral width at half height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	20	-	nm
Reverse Current	I_R	$I_F = 20\text{mA}$	-	-	100	μA
Luminous Intensity	I_v	$I_F = 20\text{mA}$	90	-	-	mcd
			110	-	-	
			140	-	-	

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